

2812

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail, with sufficient postage, in an envelope addressed to: Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450, on the below date:
Date: December 4, 2006 Name: Jasper W. Dockrey Signature: [Signature]

BRINKS
HOFFER
GILSON
& LIONE

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. of: Fournel et al.

Appln. No.: 10/538,482

Filed: March 17, 2006

For: METHOD FOR MAKING A STRESSED
STRUCTURE DESIGNED TO BE
DISSOCIATED

Examiner: Lebentritt,
Michael

Art Unit: 2812

Attorney Docket No: 9905/28

Mail Stop Amendment
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

Sir:

Attached is/are:

☒ Transmittal Letter; First Supplemental Information Disclosure Statement; Form PTO-1449; cited references B50-B110 and reply postcard.

☒ Return Receipt Postcard

Fee calculation:

☒ No additional fee is required.

☐ Small Entity.

☐ An extension fee in an amount of \$_____ for a _____-month extension of time under 37 C.F.R. § 1.136(a).

☐ A petition or processing fee in an amount of \$_____ under 37 C.F.R. § 1.17(____).

☐ An additional filing fee has been calculated as shown below:

	Claims Remaining After Amendment		Highest No. Previously Paid For	Present Extra	Small Entity		or	Not a Small Entity	
					Rate	Add'l Fee		Rate	Add'l Fee
Total		Minus			x \$25=			x \$50=	
Indep.		Minus			x 100=			x \$200=	
First Presentation of Multiple Dep. Claim					+\$180=			+\$360=	
					Total	\$		Total	\$

Fee payment:

☐ A check in the amount of \$_____ is enclosed.

☐ Please charge Deposit Account No. 23-1925 in the amount of \$_____. A copy of the transmittal is enclosed for this purpose.

☐ Payment by credit card in the amount of \$_____ (Form PTO-2038 is attached).

☒ The Director is hereby authorized to charge payment of any additional filing fees required under 37 CFR § 1.16 and any patent application processing fees under 37 CFR § 1.17 associated with this paper (including any extension fee required to ensure that this paper is timely filed), or to credit any overpayment, to Deposit Account No. 23-1925.

Respectfully submitted,

December 4, 2006

Date

[Signature]
Jasper W. Dockrey (Reg. No. 33,868)

BRINKS HOFFER GILSON & LIONE

NBC Tower – Suite 3600, 455 N. Cityfront Plaza Drive, Chicago, IL 60611-5599

BRINKS
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FORM PTO-1429	SERIAL NO. 10/538,482	CASE NO. 9905/28
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE March 17, 2006	GROUP ART UNIT 2812
(use several sheets if necessary)		APPLICANT(S): Fournel et al.

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
	B1	4,028,149	6/7/1977	Deines et al.		
	B2	5,242,863	9/7/1993	Xiang-Zheng et al.		
	B3	5,300,788	4/5/1994	Fan et al.		
	B4	5,405,802	4/11/1995	Yamagata et al.		
	B5	5,559,043	9/24/1996	Bruel		
	B6	5,811,348	9/22/1998	Matushita et al.		
	B7	5,854,123	12/29/1998	Sato et al.		
	B8	5,877,070	3/2/1999	Goesele et al.		
	B9	5,909,627	6/1/1999	Egloff		
	B10	5,920,764	7/6/1999	Hanson et al.		
	B11	5,953,622	9/14/1999	Lee et al.		
	B12	5,966,620	10/12/1999	Sakaguchi et al.		
	B13	5,993,677	11/30/1999	Biasse et al.		
	B14	5,994,207	11/30/1999	Henley et al.		
	B15	6,013,563	1/11/2000	Henley et al.		
	B16	6,020,252	2/1/2000	Aspar et al.		
	B17	6,048,411	4/11/2000	Henley et al.		
	B18	6,054,370	4/25/2000	Doyle		
	B19	6,071,795	6/6/2000	Cheung et al.		
	B20	6,103,597	8/15/2000	Aspar et al.		
	B21	6,103,599	8/15/2000	Henley et al.		
	B22	6,127,199	10/3/2000	Inoue		
	B23	6,146,979	11/14/2000	Henley et al.		
	B24	6,150,239	11/21/2000	Goesele et al.		
	B25	6,190,998	2/20/2001	Bruel et al.		
	B26	6,225,190	5/1/2001	Bruel et al.		
	B27	6,225,192	5/1/2001	Aspar et al.		
	B28	6,271,101	8/7/2001	Fukunaga		
	B29	6,303,468	10/16/2001	Aspar et al.		
	B30	6,323,108	11/27/2001	Kub et al.		
	B31	6,323,109	11/27/2001	Okonogi		
	B32	6,346,458	2/12/2002	Bower		
	B33	6,362,077	3/26/2002	Aspar et al.		
	B34	6,513,564	2/4/2003	Bryan et al.		
	B35	6,534,380	3/18/2003	Yamauchi et al.		
	B36	6,593,212	7/15/2003	Kub et al.		
	B37	6,607,969	8/19/2003	Kub et al.		

EXAMINER	DATE CONSIDERED
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FORM PTO-1449	SERIAL NO. 10/538,482	CASE NO. 9905/28
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE March 17, 2006	GROUP ART UNIT 2812
(use several sheets if necessary)		APPLICANT(S): Fourenel et al.

REFERENCE DESIGNATION

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	B38	6,727,549	4/27/2004	Doyle		
	B39	6,756,286	6/29/2004	Moriceau et al.		
	B40	6,770,507	8/3/2004	Abe et al.		
	B41	6,946,365	9/20/2005	Aspar et al.		
	B42	2002/0025604	2/28/2002	Tiwari		
	B43	2002/0153563	10/24/2002	Ogura		
	B44	2002/0185684	12/12/2002	Campbell et al.		
	B45	2003/0077885	4/24/2003	Aspar et al.		
	B46	2003/0134489	7/17/2003	Schwarzenbach et al.		
	B47	2003/0162367	8/28/2003	Roche		
	B48	2003/0199105	10/23/2003	Kub et al.		
	B49	2004/0144487	7/29/2004	Martinez et al.		

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO
	B50	EP 0 293 049 B1	9/29/1993	Europe		
	B51	EP 0 533 551 B1	3/9/2000	Europe		Abstract
	B52	EP 0 717 437 B1	4/24/2002	Europe		
	B53	EP 0 767 486 B1	1/2/2004	Europe		
	B54	EP 0 786 801A1	6/18/2003	Europe		Abstract
	B55	EP 0 793 263 A2	9/3/1997	Europe		
	B56	EP 0 801 419 A1	10/15/1997	Europe		Abstract
	B57	EP 0 807 970 A1	11/19/1997	Europe		Abstract
	B58	EP 0 902 843 B1	3/29/2000	Europe		Abstract
	B59	EP 0 917 193 A1	5/19/1999	Europe		
	B60	EP 0 925 888 B1	11/10/2004	Europe		
	B61	EP 0 938 129 A1	8/25/1999	Europe		
	B62	EP 0 994 503 A1	4/19/2000	Europe		Abstract
	B63	EP 1 014 452 B1	5/3/2006	Europe		
	B64	FR 2 748 850 A1	11/21/1997	France		Abstract
	B65	FR 2 748 851	11/21/1997	France		Abstract
	B66	FR 2 758 907 A1	7/31/1998	France		Abstract
	B67	FR 2 767 416 A1	2/19/1999	France		Abstract
	B68	FR 2 773 261	7/2/1999	France		Abstract
	B69	FR 2 774 510 A1	8/6/1999	France		Abstract
	B70	FR 2 781 925 A1	2/4/2000	France		Abstract
	B71	FR 2 796 491	1/19/01	France		Abstract

EXAMINER

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(use several sheets if necessary)	APPLICANT(S): Fourenel et al.	

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER Number-Kind Code (if known)	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO
	B72	FR 2 797 347	2/9/2001	France		Abstract
	B73	FR 2 809 867	12/7/2001	France		Abstract
	B74	FR 2 847 075 A1	5/14/2004	France		Abstract
	B75	JP 62265717	11/18/1987	Japan		Abstract
	B76	JP 07-254690	10/3/1995	Japan		Abstract
	B77	JP 7-302889	11/14/1995	Japan		Abstract
	B78	JP 09-213594	8/15/1997	Japan		Abstract
	B79	JP 09-307719	11/28/1997	Japan		Abstract
	B80	JP 11045862	2/16/1999	Japan		Abstract
	B81	JP 11074208	3/16/1999	Japan		Abstract
	B82	JP 11-87668	3/30/1999	Japan		Abstract
	B83	JP 11-145436	5/28/1999	Japan		Abstract
	B84	JP 11-233449	8/27/1999	Japan		Abstract
	B85	WO 99/08316	2/18/1999	WIPO		Abstract
	B86	WO 99/35674 A1	7/15/1999	WIPO		Abstract
	B87	WO 99/39378	8/5/1999	WIPO		
	B88	WO 00/63965	10/26/2000	WIPO		
	B89	WO 01/11930A2	2/15/2001	WIPO		
	B90	WO 02/47156 A1	6/13/2002	WIPO		Abstract
	B91	WO 02/083387 A1	10/24/2002	WIPO		Abstract
	B92	WO 03/013815	2/20/2003	WIPO		Abstract
	B93	WO 04/044976	5/27/2004	WIPO		Abstract

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	B94	Agarwal et al "Efficient production of Silicon-on-insulator films by co-implatation of HE ⁺ with H ⁺ ", <i>Applied Physics Letter, American Institute of Physics</i> , Vol. 72, No. 9, March 1998, pp. 1086-1088
	B95	Bruel et al., [Vol. 99-1] Meeting Abstract No. 333, "Single-crystal semiconductor layer delamination and transfer through hydrogen implantation," <i>The 195th Metting of The Electrochemical Society</i> , May 2-6, 1999, Seattle, Washington
	B96	Camperi-Ginestet et al., "Alignable Epitaxial Liffoff of GaAs Materials with Selective Deposition Using Polyimide Diaphragms", <i>IEEE Transactions Photonics Technology Letters</i> , Vol. 3, No. 12, December 1991, pp. 1123-1126
	B97	Cerofolini et al. "Ultradense Gas Bubbles in Hydrogen-or-Helium-Implanted (or Co-implanted) Silicon", <i>Materials Science and Engineering</i> , B71, 2000, pp. 196-202

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(use several sheets if necessary)		APPLICANT(S): Fourenel et al.

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	B98	Demeester, et al., "Epitaxial Lift-off and its Applications", <i>Semicond. Sci. Technol.</i> , Vol. 8, 1993, pp. 1124-1135
	B99	DiCioccio et al., "III-V layer transfer onto silicon and applications", <i>Phys. Stat. Sol. (a)</i> , Vol. 202, No. 4., 2005, pp. 509-515/DOI 10.1002/pssa. 200460411
	B100	Hamaguchi, et al., "Novel LSI/SOI Wafer Fabrication Using Device Layer Transfer Technique" <i>Proc. IEDM</i> , 1985, pp. 688-691
	B101	Henttinen et al. "Mechanically induced Si Layer Transfer in Hydrogen-Implanted Si-Wafers", <i>American Institute of Physics</i> , Vol. 76, No. 17, April 2000, pp. 2370-2372
	B102	Kucheyev et al., "Ion implantation into GaN", <i>Materials Science and Engineering</i> , 33, 2001, pp. 51-107
	B103	Liu et al., "Ion implantation in GaN at liquid-nitrogen temperature: Structural characteristics and amorphization," <i>Physical Review B of The American Physical Society</i> , Vol. 57, No. 4, 1988, pp. 2530-2535
	B104	Moriceau et al., [Vol. 99-1] Meeting Abstract No. 405, "A New Characterization Process Used to Qualify SOI Films," <i>The 195th Meeting of The Electrochemical Society</i> , May 2-6, 1999, Seattle, Washington.
	B105	Pollentier et al., "Fabrication of High-Radiance LEDs by Epitaxial Lift-off" <i>SPIE</i> , Vol. 1361, 1990, pp. 1056-1062
	B106	Suzuki et al., "High-Speed and Low Power n ⁺ -p ⁺ Double-Gate SOI CMOS", <i>IEICE Trans. Electron.</i> , Vol. E78-C, No. 4, April 1995, pp. 360-367
	B107	Tong et al, "Low Temperature Si Layer Splitting", <i>Proceedings 1997 IEEE International SOI Conference</i> , Oct. 1997, pgs. 126-127
	B108	Wong et al., "Integration of GaN Thin Films with Dissimilar Substrate Materials by Pd-In Metal Bonding and Laser Lift-off", <i>Journal of Electronic Materials</i> , Vol. 28, No. 12, 1999, pp. 1409-1413
	B109	Yun et al., "Fractional Implantation Area Effects on Patterned Ion-Cut Silicon Layer Transfer," Dept. of Electrical Eng. And Computer Sciences, University of California, Berkeley, CA 94720, USA, 1999 IEEE International SOI Conference, Oct. 1999, pg. 129-30
	B110	Yun et al., "Thermal and Mechanical Separations of Silicon Layers from Hydrogen Pattern-Implanted Wafers," <i>Journal of Electronic Materials</i> , Vol. No. 36, No. 8 2001

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. of: FOURNEL ET AL.

Appln. No.: 10/538,482

Filed: March 17, 2006

For: METHOD FOR MAKING A
STRESSED STRUCTURE
DESIGNED TO BE
DISSOCIATED

Examiner: Lebentritt, Michael

Art Unit: 2812

Attorney Docket No: 9905/28

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

In accordance with the duty of disclosure under 37 C.F.R. §1.56 and §§1.97-1.98, and more particularly in accordance with 37 C.F.R. §1.97(b), Applicants hereby cite the following reference(s):

DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	NAME
4,028,149	6/7/1977	Deines et al.
5,242,863	9/7/1993	Xiang-Zheng et al.
5,300,788	4/5/1994	Fan et al.
5,405,802	4/11/1995	Yamagata et al.
5,559,043	9/24/1996	Bruehl
5,811,348	9/22/1998	Matushita et al.
5,854,123	12/29/1998	Sato et al.
5,877,070	3/2/1999	Goesele et al.
5,909,627	6/1/1999	Egloff
5,920,764	7/6/1999	Hanson et al.
5,953,622	9/14/1999	Lee et al.
5,966,620	10/12/1999	Sakaguchi et al.
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5,994,207	11/30/1999	Henley et al.
6,013,563	1/11/2000	Henley et al.
6,020,252	2/1/2000	Aspar et al.
6,048,411	4/11/2000	Henley et al.
6,054,370	4/25/2000	Doyle
6,071,795	6/6/2000	Cheung et al.
6,103,597	8/15/2000	Aspar et al.
6,103,599	8/15/2000	Henley et al.
6,127,199	10/3/2000	Inoue
6,146,979	11/14/2000	Henley et al.
6,150,239	11/21/2000	Goesele et al.

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6,303,468	10/16/2001	Aspar et al.
6,323,108	11/27/2001	Kub et al.
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6,346,458	2/12/2002	Bower
6,362,077	3/26/2002	Aspar et al.
6,513,564	2/4/2003	Bryan et al.
6,534,380	3/18/2003	Yamauchi et al.
6,593,212	7/15/2003	Kub et al.
6,607,969	8/19/2003	Kub et al.
6,727,549	4/27/2004	Doyle
6,756,286	6/29/2004	Moriceau et al.
6,770,507	8/3/2004	Abe et al.
6,946,365	9/20/2005	Aspar et al.
2002/0025604	2/28/2002	Tiwari
2002/0153563	10/24/2002	Ogura
2002/0185684	12/12/2002	Campbell et al.
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2003/0134489	7/17/2003	Schwarzenbach et al.
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EP 0 994 503 A1	4/19/2000	Europe
EP 1 014 452 B1	5/3/2006	Europe
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FR 2 758 907 A1	7/31/1998	France
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JP 11074208	3/16/1999	Japan
JP 11-87668	3/30/1999	Japan
JP 11-145436	5/28/1999	Japan
JP 11-233449	8/27/1999	Japan
WO 99/08316	2/18/1999	WIPO
WO 99/35674 A1	7/15/1999	WIPO
WO 99/39378	8/5/1999	WIPO
WO 00/63965	10/26/2000	WIPO
WO 01/11930A2	2/15/2001	WIPO
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WO 02/083387 A1	10/24/2002	WIPO
WO 03/013815	2/20/2003	WIPO
WO 04/044976	5/27/2004	WIPO

OTHER DOCUMENTS

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Tong et al, "Low Temperature SI Layer Splitting", <i>Proceedings 1997 IEEE International SOI Conference</i> , Oct. 1997, pgs. 126-127
Wong et al., "Integration of GaN Thin Films with Dissimilar Substrate Materials by Pd-In Metal Bonding and Laser Lift-off", <i>Journal of Electronic Materials</i> , Vol. 28, No. 12, 1999, pp. 1409-1413
Yun et al., "Fractional Implantation Area Effects on Patterned Ion-Cut Silicon Layer Transfer," Dept. of Electrical Eng. And Computer Sciences, University of California, Berkeley, CA 94720, USA, 1999 IEEE International SOI Conference, Oct. 1999, pg. 129-30
Yun et al., "Thermal and Mechanical Separations of Silicon Layers from Hydrogen Pattern-Implanted Wafers," <i>Journal of Electronic Materials</i> , Vol. No. 36, No. 8 2001

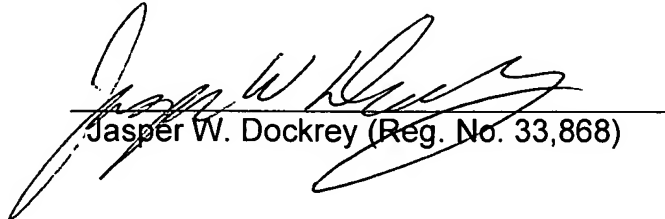
Applicants are enclosing Form PTO-1449 (four sheets), along with a copy of each listed reference for which a copy is required under 37 C.F.R. §1.98(a)(2). As each of the listed references is in English, no further commentary is believed to be necessary, 37 C.F.R §1.98(a)(3). Applicants respectfully request the Examiner's consideration of the above reference(s) and entry thereof into the record of this application.

By submitting this Statement, Applicants are attempting to fully comply with the duty of candor and good faith mandated by 37 C.F.R. §1.56. As such, this Statement is not intended to constitute an admission that any of the enclosed references, or other information referred to therein, constitutes "prior art" or is otherwise "material to patentability," as that phrase is defined in 37 C.F.R. §1.56(a).

Applicants have calculated no fee to be due in connection with the filing of this Statement. However, the Director is authorized to charge any fee deficiency associated with the filing of this Statement to a deposit account, as authorized in the Transmittal accompanying this Statement.

Respectfully submitted,

December 4, 2006
Date


Jasper W. Dockrey (Reg. No. 33,868)